

FIN-TYPE RESISTORS

Abstract of the Disclosure

A method of forming a Fin structure including a resistor present in the thin vertically oriented semiconductor body is provided. The method includes the steps of forming at least one vertically-oriented semiconductor body having exposed vertical surfaces on a substrate; implanting dopant ions into the exposed vertical surfaces of the at least one semiconductor body off-axis at a concentration and energy sufficient to penetrate into the exposed vertical surfaces of the at least one semiconductor body without saturation; and forming contacts to the at least one semiconductor body. The present invention is directed to a Fin structure which includes a resistor present within the thin vertically oriented semiconductor body.

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